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March 2015

# FGH75N60UF 600 V, 75 A Field Stop IGBT

### **Features**

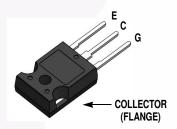
- · High Current Capability
- Low Saturation Voltage: V<sub>CE(sat)</sub> = 1.9 V @ I<sub>C</sub> = 75 A
- · High Input Impedance
- Fast Switching
- · RoHS Compliant

### **Applications**

· Solar Inverter, UPS, Welder, PFC

### **General Description**

Using novel field stop IGBT technology, Fairchild's field stop IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.





### **Absolute Maximum Ratings**

Symbol	Description		Ratings	Unit
V <sub>CES</sub>	Collector to Emitter Voltage		600	V
V	Gate to Emitter Voltage		±20	V
$V_{GES}$	Transient Gate-to-Emitter Voltage		±30	V
lo	Collector Current	$@T_C = 25^{\circ}C$	150	Α
IC	Collector Current	$@ T_C = 100^{\circ}C$	75	Α
I <sub>CM (1)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	225	Α
P <sub>D</sub>	Maximum Power Dissipation	$@ T_C = 25^{\circ}C$	452	W
י ט	Maximum Power Dissipation	$@ T_C = 100^{\circ}C$	181	W
T <sub>J</sub>	Operating Junction Temperature		-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

1: Repetitive rating: Pulse width limited by max. junction temperature

### **Thermal Characteristics**

Symbol	Symbol Parameter		Max.	Unit	
$R_{\theta JC}(IGBT)$	R <sub>0JC</sub> (IGBT) Thermal Resistance, Junction to Case		0.276	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W	

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH75N60UFTU	FGH75N60UF	TO-247	Tube	N/A	N/A	30

# Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \mu\text{A}$	600	-	-	V
$\Delta BV_{CES}$ / $\Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \mu\text{A}$	-	0.75	-	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0 V	-	-	250	μΑ
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_C = 250 \mu\text{A},  V_{CE} = V_{GE}$	4.0	5.0	6.5	V
GE(III)		I <sub>C</sub> = 75 A, V <sub>GE</sub> = 15 V	_	1.9	2.4	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 75 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 125°C	-	2.15	-	V
Dynamic C	characteristics				1	
C <sub>ies</sub>	Input Capacitance		-	3850	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1  MHz	-	375	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	- 1 = 1 IVII IZ	-	147	-	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{CC}$ = 400 V, $I_{C}$ = 75 A, $R_{G}$ = 3 $\Omega$ , $V_{GE}$ = 15 V, Inductive Load, $T_{C}$ = 25°C	-	27	-	ns
t <sub>r</sub>	Rise Time		-	70	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		-	128	-	ns
t <sub>f</sub>	Fall Time		-	30	80	ns
E <sub>on</sub>	Turn-On Switching Loss		-	3.05	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		- /	1.35	-	mJ
E <sub>ts</sub>	Total Switching Loss		-	4.4	-	mJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	27	- /	ns
t <sub>r</sub>	Rise Time		-	74	- 7	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 75 \text{ A},$ $R_{G} = 3 \Omega, V_{GE} = 15 \text{ V},$ Inductive Load, $T_{C} = 125^{\circ}\text{C}$	-	153	-	ns
t <sub>f</sub>	Fall Time		-	35	-	ns
E <sub>on</sub>	Turn-On Switching Loss		-	3.6	- /	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	1.8	- [	mJ
E <sub>ts</sub>	Total Switching Loss		-	5.4	- \	mJ
Qg	Total Gate Charge		-	250	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	$V_{CE} = 400 \text{ V}, I_{C} = 75 \text{ A},$ $V_{GE} = 15 \text{ V}$	-	30	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	v <sub>GE</sub> = 15 v	-	130	-	nC

Figure 1. Typical Output Characteristics

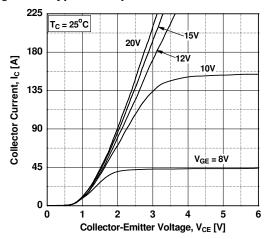


Figure 3. Typical Saturation Voltage Characteristics

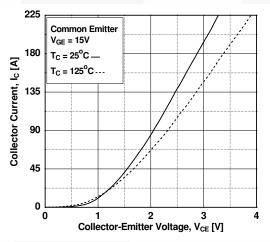
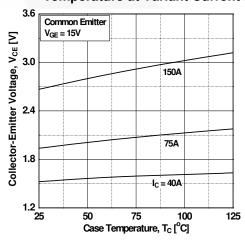


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level



**Figure 2. Typical Output Characteristics** 

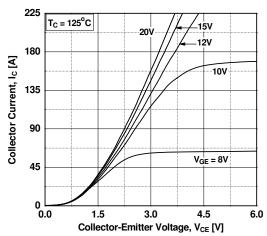


Figure 4. Transfer Characteristics

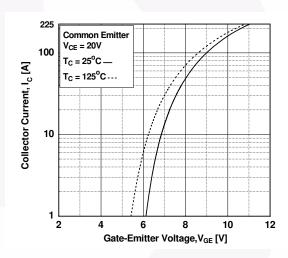


Figure 6. Saturation Voltage vs.  $V_{GE}$ 

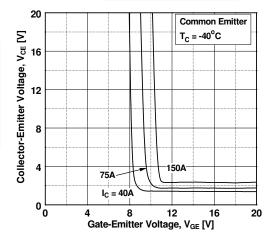


Figure 7. Saturation Voltage vs. V<sub>GE</sub>

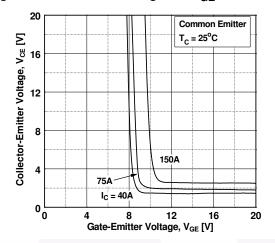


Figure 8. Saturation Voltage vs. V<sub>GE</sub>

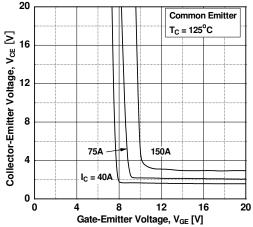


Figure 9. Capacitance Characteristics

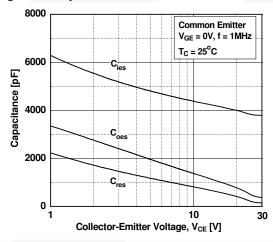


Figure 10. Gate charge Characteristics

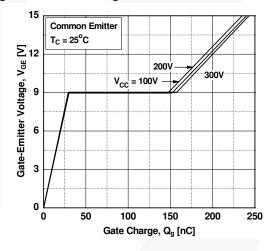


Figure 11. SOA Characteristics

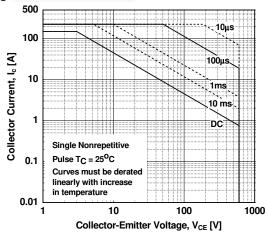


Figure 12. Load Current vs. Frequency

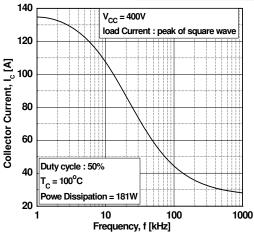


Figure 13. Turn-on Characteristics vs.
Gate Resistance

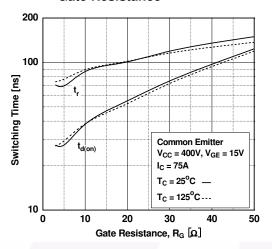


Figure 15. Turn-on Characteristics vs. Collector Current

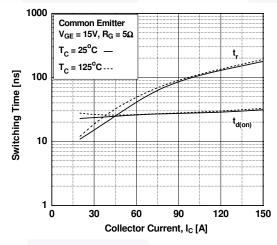


Figure 17. Switching Loss vs. Gate Resistance

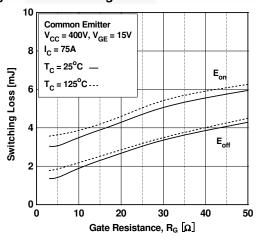


Figure 14. Turn-off Characteristics vs. Gate Resistance

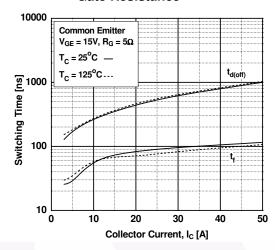


Figure 16. Turn-off Characteristics vs. Collector Current

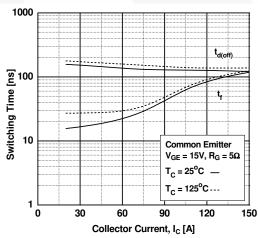


Figure 18. Switching Loss vs. Collector Current

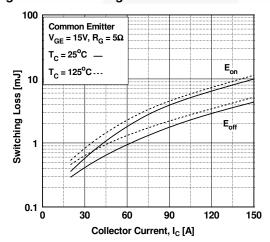


Figure 19. Turn off Switching SOA Characteristics

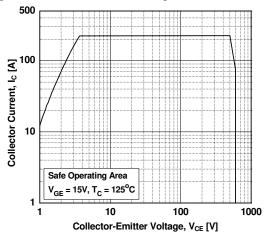
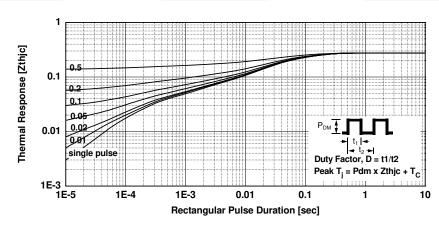
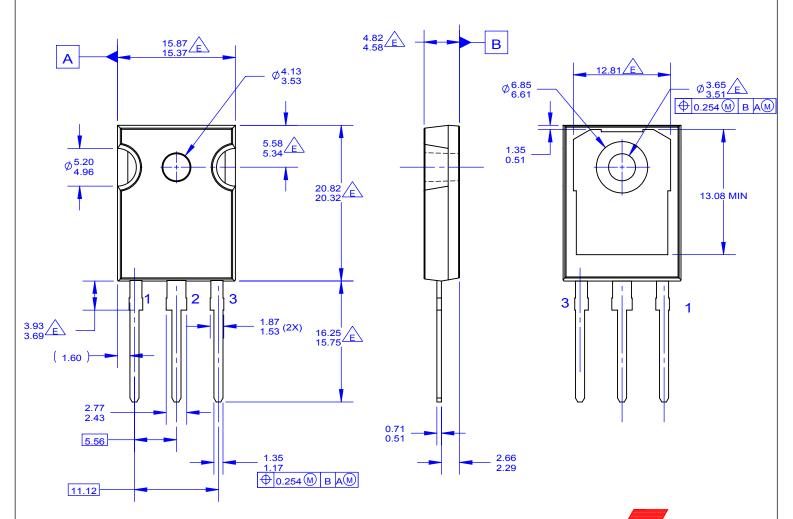


Figure 20. Transient Thermal Impedance of IGBT







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